

Motivation

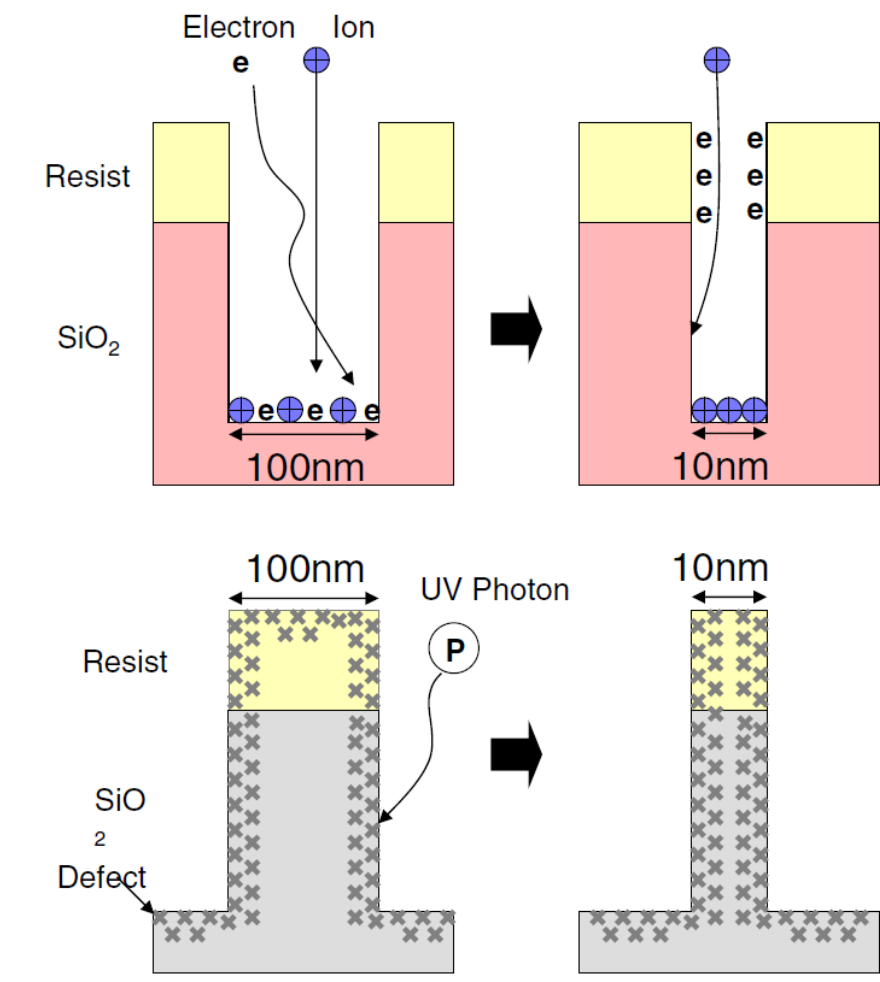
- Plasma etching and deposition are essential for microelectronics fabrication, requiring **precise** control of ion **energy and angular distributions (EADs)** hitting the wafer to enable critical surface reactions.

- However, **plasma processes** can negatively impact **electrical** and **optical** properties of nanodevices due to:

- (1) **Differential charging of features** - distorts ion trajectories leading to defects (e.g. bowing) or ARDE.
- (2) **UV photons** - can cause surface defects (dangling bonds).

- These effects should become more pronounced as device dimensions shrink, especially in **2-dimensional devices** with near monolayer thickness.

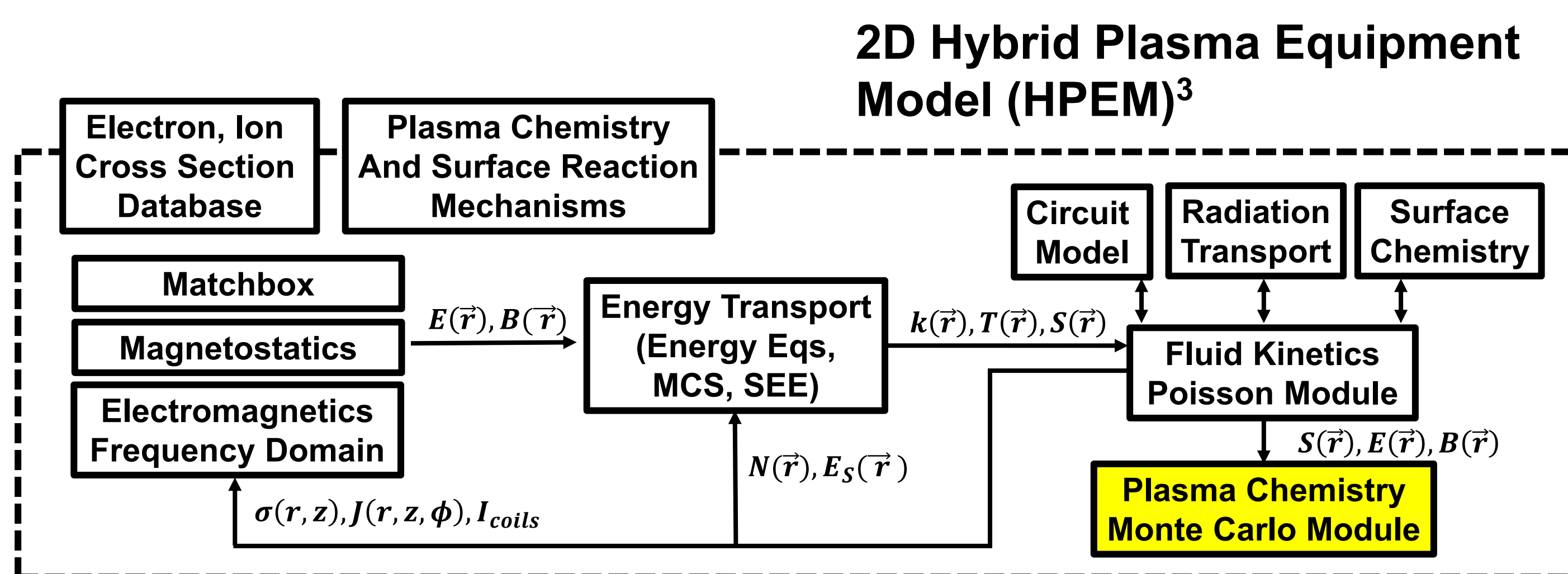
- Energetic neutral beams** offer a potential **damage-free** alternative for nanoscale fabrication².



Impact of Differential Charging (top) and UV exposure (bottom) on nanoscale devices as feature sizes decrease.¹

How can we control and optimize the energy and angular distribution of neutrals hitting the wafer?

Modelling Tool



- HPEM is a simulation tool which combines **kinetic** and **fluid** methods to model the physical and chemical behavior of **low-temperature plasmas**.

- The **Plasma Chemistry Monte Carlo (PCMC)** module uses source terms and electric/magnetic fields from HPEM to launch and track ion and neutral particles until they hit a surface.

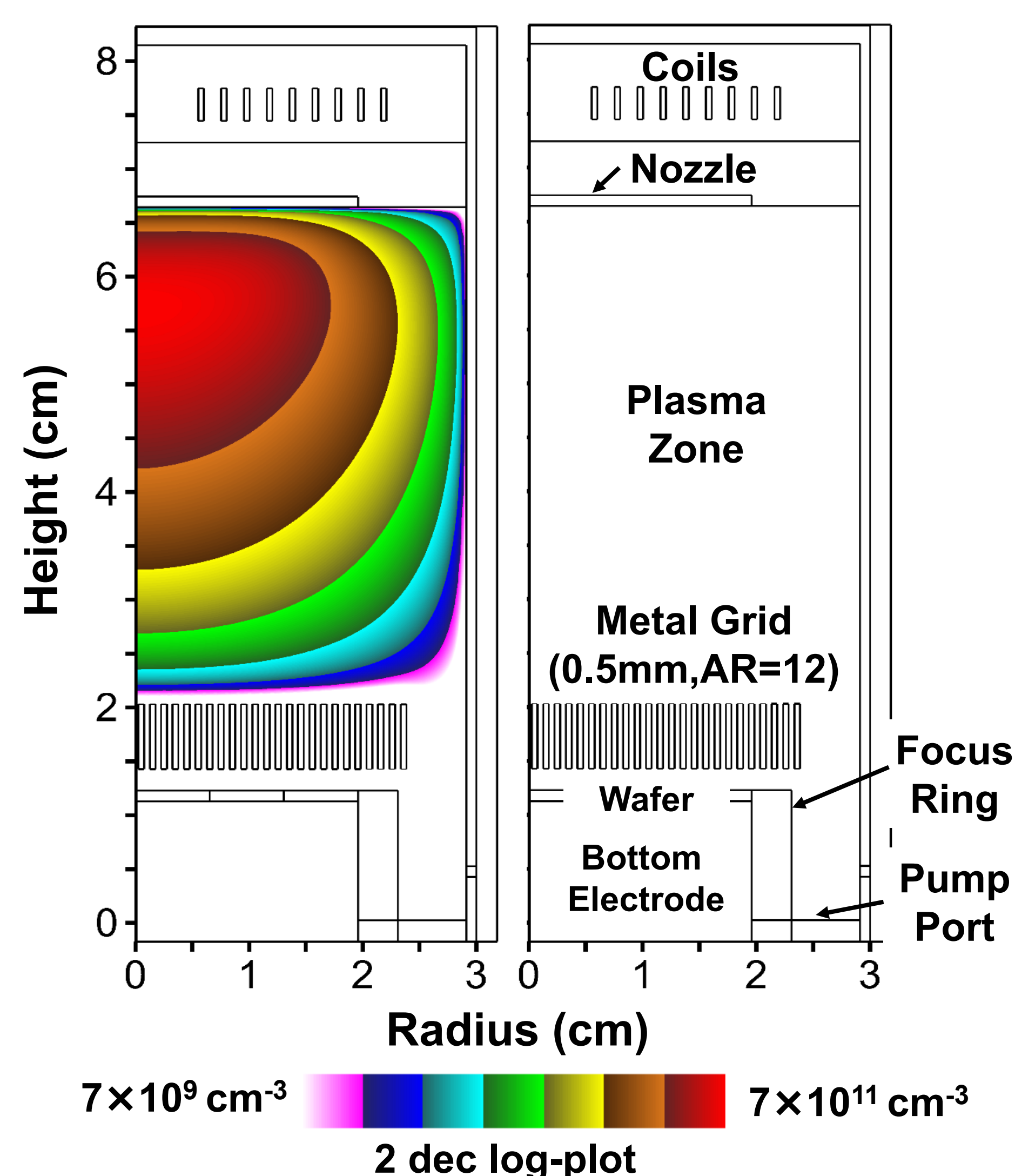
Neutral Beam Reactor Geometry

- Neutral beams** can be generated by **accelerating ions** toward a **biased grid**, where they **reflect** and **neutralize** on the aperture walls.
- HPEM has been improved to model **ion reflection** from the grid, enabling the calculation of **energy and angular distributions of the neutrals** hitting the grid.

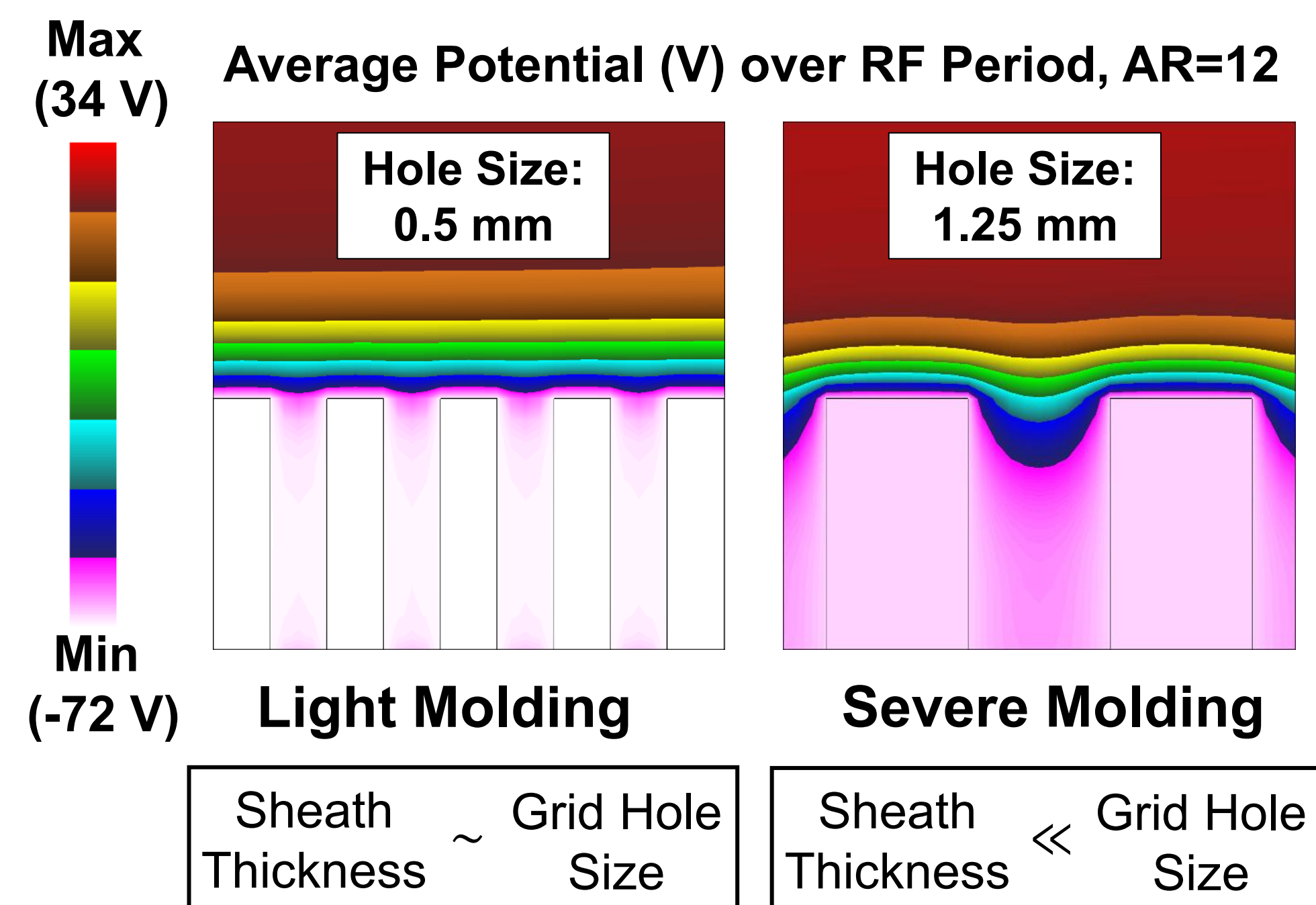
- Inductively Coupled Plasma (ICP)** at **50 W**.
- Argon** at 20 mTorr and 400 K.
- Metal grid with RF bias:** 100 V, 10 MHz.
- Bottom Electrode grounded.
- Variable **Grid Hole Size** (0.5-1.25 mm) and **aspect ratio** (6-24).

- Assumptions:**

- (1) Charge-exchange reactions are not considered.
- (2) All argon ions reflect **elastically** and **specularly** from the grid as ground state neutrals.



Effect of Plasma Molding

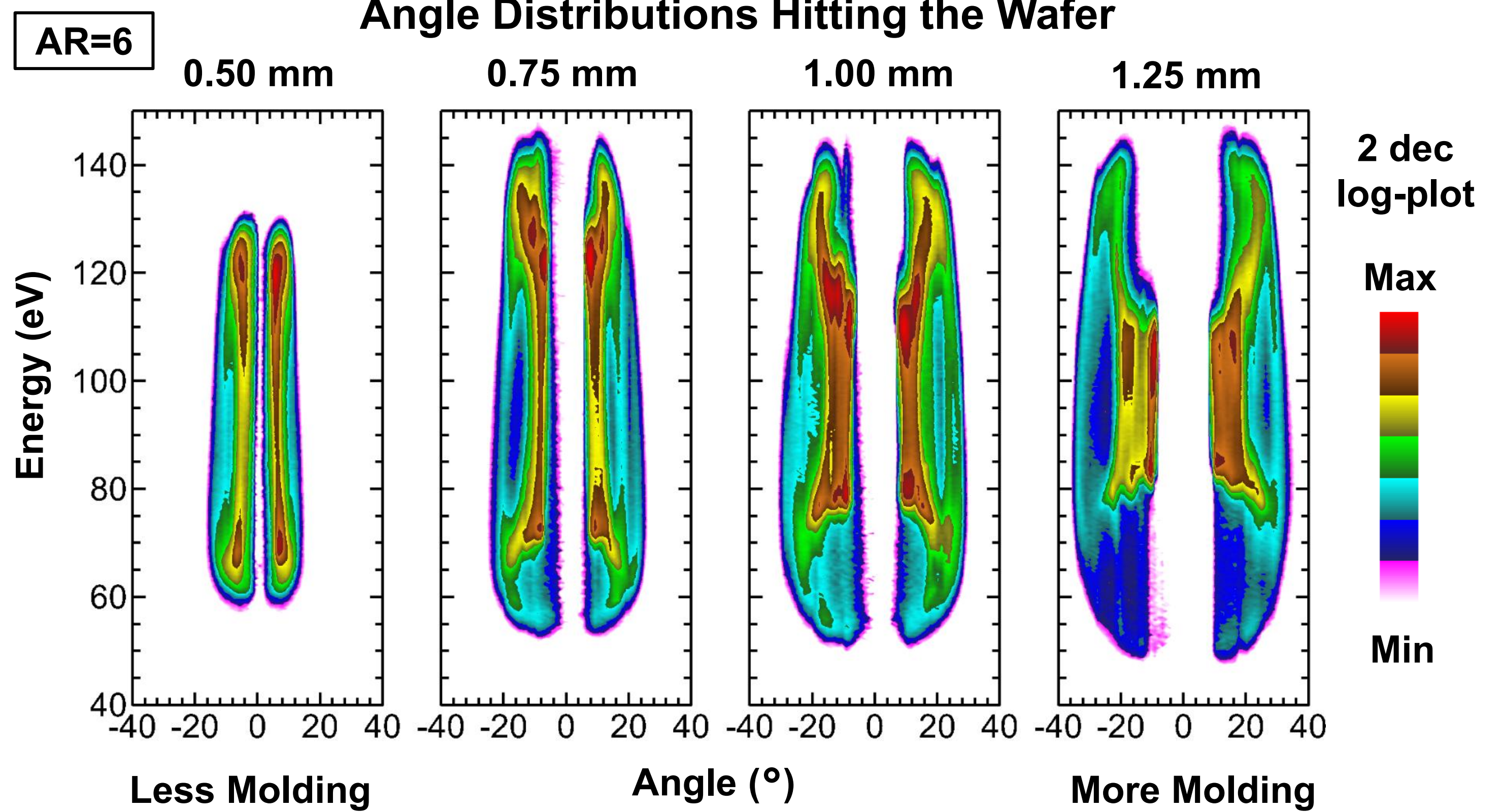


The degree of **plasma molding** over the grid holes influences the ion trajectories⁴.

Severe plasma molding favors **stronger ion deflection** toward the grid.

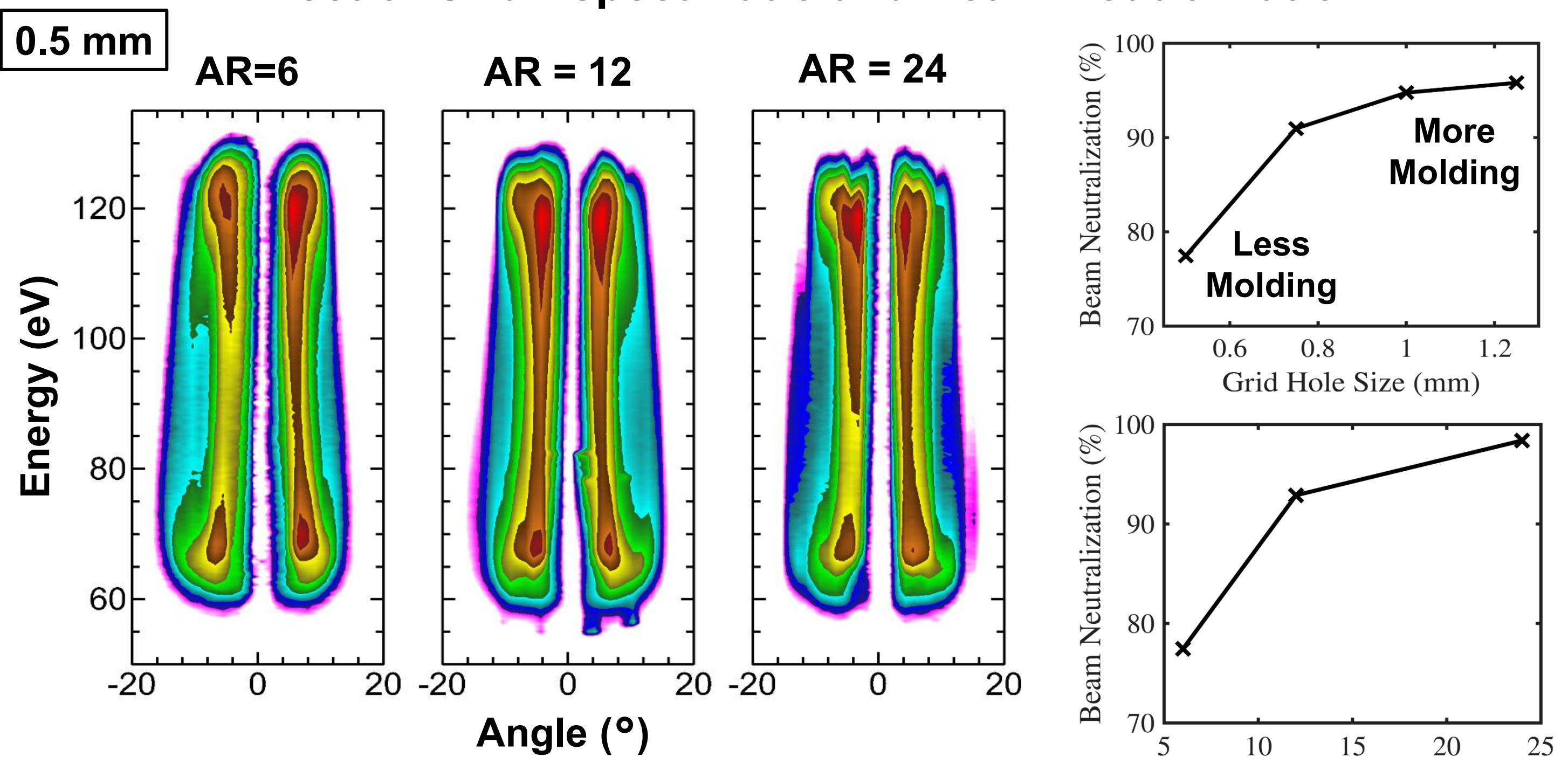
Higher neutralization but reflected neutrals hit grid with **larger angles**.

Effect of Grid Hole Size on the Neutral Energy and Angle Distributions Hitting the Wafer



- Few neutrals at very small angles (ions must be deflected to collide with grid).
- Lighter molding** leads to **angularly-narrow distributions** and **severe molding** to **broadier distributions with complex shapes** (curved sheath).

Effect of Grid Aspect Ratio and Beam Neutralization



- Varying **aspect ratio** does not change the distribution function significantly (plasma molding is a local phenomenon).
- Beam neutralization** is **lower for lighter molding** but can be **increased independently** by increasing the **grid aspect ratio**.

Summary

- In principle, neutral beams with **tunable energy and angular distributions** can be achieved while maintaining **high particle fluxes** ($\sim 10^{15} - 10^{16} \text{ cm}^{-2} \text{ s}^{-1}$).
- Plasma sheath molding** plays a key role in defining the distribution functions and can be controlled by adjusting the **grid aperture** and/or **plasma parameters**.
- To achieve an optimal **narrow-angle hot neutral distribution**, the grid geometry and operating conditions should be tuned to obtain **light sheath molding**.
- Beam neutralization** can be improved by increasing the grid **aspect ratio**.

References

- [1] S. Samukawa 2015 ECS J. Solid State Sci. Technol. 4 N5089
- [2] S. Samukawa et al 2001 Jpn. J. Appl. Phys. 40 L779
- [3] M. J. Kushner, J. Phys. D. 42, 194013 (2009).
- [4] D. J. Economou 2008 J. Phys. D: Appl. Phys. 41 024001

Acknowledgements:

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